

**Complete if Known**

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(Use as many sheets as necessary)*

Sheet	1	of	1
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Application Number	
Filing Date	09-17-2003
First Named Inventor	SHI ET AL
Art Unit	25
Examiner Name	Thom
Attorney Docket Number	P120-US

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Examiner  
Signature

Brand Thomas

Date	Considered
10/1/80	10/1/80
10/2/80	10/2/80
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10/31/80	10/31/80

9/7/02

Examiner Signature	<i>Brand Thomas</i>	Considered	<i>11/6/1</i>
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>			
		Application Number	10/666,002		
		Filing Date	9/17/03		
		First Named Inventor	Shi		
		Art Unit	Not Yet Assigned <i>2873</i>		
		Examiner Name	Not Yet Assigned <i>Thomas</i>		
Sheet	1	of	6	Attorney Docket Number	P120-US

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Document Number Number - Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
BNT		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwaj, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
		US- 6,162,367	12-19-2000	Tai et al.	
		US- 6,290,864 B1	09-18-2001	Patel et al.	
		US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
		US- 2001/0002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
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		US- 2002/0185699	12-12-2002	Reid	
		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
	BNT		US- 5,835,256	11-10-1998	Huibers, A.
		US- 2002/0047172 A1	04-25-2002	Reid	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

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Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	-Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
BNT		EP-0704884-A2		04-03-1998	Mehta, J.		
		EP-0822582-A2		02-04-1998	Bhardwaj, J.K.		
		EP-0822584-A2		04-04-1998	Bhardwaj, J.K.		
		WO-99/49506		09-30-1999	McQuarrie, A.D.		
		EP-0878824-A2		11-18-1998	McQuarrie et al.		
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		JP-1982/57098679-A		06-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A		08-04-1983	Yoshihiro et al.		
BNT		JP-1985/60057938-A		04-03-1985	Katsumi et al.		
		WO-98/32163		07-23-1998	Tai et al.		

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		Application Number	10/666.002
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Filing Date	9/17/03
		First Named Inventor	Shi
		Art Unit	Not Yet Assigned <i>2873</i>
		Examiner Name	Not Yet Assigned <i>Thomas</i>
Sheet	2	of	6
		Attorney Docket Number	P120-US

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BNT		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leung, et al.	
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		US- 6,204,080	03-20-2001	Hwang	
		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
		US- 2002/0164879 A1	11/07/02	Leung, et al.	
		US- 2002/0163051 A1	11/07/02	Gopal, et al.	
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		US- 6,500,356 B2	12/31/02	Goto, et al.	
		US- 2003/0124848 A1	07/03/03	Chinn, et al.	
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
BNT		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		JP-1986/61187238-A	08-20-1986	Nobuo et al.		
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		JP-1987/62071217-A	04-01-1987	Toru et al.		
		JP-1988/63155713-A	06-28-1988	Tadashi, F.		
		JP-1986/61053732-A	03-17-1986	Arata et al.		
		JP-1986/61134019-A	06-21-1986	Shinii et al.		
		JP-1986/61181131-A	08-13-1986	Shinii et al.		

Examiner Signature	<i>Brand Thomas</i>	Date Considered	<i>9/2/05</i>
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Application Number				10/666,002	
Filing Date				9/17/03	
First Named Inventor				Shi	
Art Unit				Not Yet Assigned <i>2873</i>	
Examiner Name				Not Yet Assigned <i>Thomas</i>	
Attorney Docket Number				P120-US	
Sheet	3	of	6		

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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
BNT		JP-1989/01208834-A	08-22-1989	Nobuo et al.		
		JP-1989/10217921-A	08-31-1989	Tsuneo et al.		
		JP-1990/02250323-A	10-08-1990	Susumu et al.		
		JP-1991/03012921-A	01-21-1991	Nobuo et al.		
		JP-1992/04096222-A	03-27-1992	Atsuyuki, A.		
BNT		JP-1995/07029823-A	01-31-1995	Hiroshi, T.		

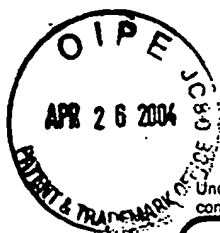
Examiner Signature	<i>Brandi Thomas</i>	Date Considered	
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/666,002
		Filing Date	9/17/03
		First Named Inventor	Shi
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned <i>Thomas</i>
		Attorney Docket Number	P120-US
Sheet	4	of	6

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
BNT		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F <sub>2</sub> and XeF <sub>2</sub> Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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		HABUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6466-6469.	
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Sheet	5	of	6	Attorney Docket Number	P120-US

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
<i>BNT</i>		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
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		"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
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<i>BNT</i>		KOHLER et al., "Fabrication of Microlenses by Plasmaless Isotropic Etching Combined with Plastic Moulding", Sens. Actuators A, Phys. (Switzerland), Vol. A53, No. 1-3 (May 1996), pp. 361-363 (abstract only).	
		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millennium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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		Group Art Unit	Not Yet Assigned 2873		
		Examiner Name	Not Yet Assigned Thomas		
Sheet	6	of	6	Attorney Docket Number	P120-US

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
BNT		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF <sub>2</sub> Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF <sub>2</sub> Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mittel 1.5- $\mu$ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
BNT		SEBEL et al., "Etching of Si Through a Thick Condensed XeF <sub>2</sub> Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

Examiner Signature	Branch Thomas	Date Considered	9/2/05
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Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/666.002
		Filing Date	9/17/03
		First Named Inventor	Shi
		Art Unit	Not Yet Assigned <i>2873</i>
		Examiner Name	Not Yet Assigned <i>Thomas</i>
Sheet	1	of	6
		Attorney Docket Number	P120-US

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
BNT		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
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		US- 6,290,864 B1	09-18-2001	Patel et al.	
		US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
		US- 2001/0002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
		US- 2002/0033229 A1	03-21-2002	Leboulitz et al.	
		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
		US- 2003/0054588 A1	03-20-2003	Patel, et al.	
		US- 5,726,480	03-10-1998	Pister, K.S.	
		US- 2002/0185699	12-12-2002	Reid	
		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
		US- 5,835,258	11-10-1998	Huibers, A.	
		US- 2002/0047172 A1	04-25-2002	Reid	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
BAT		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
		WO-99/49506	09-30-1999	McQuarrie, A.D.		
		EP-0878824-A2	11-18-1998	McQuarrie et al.		
		EP-0878824-A3	01-19-2000	McQuarrie et al.		
		JP-1982/57098679-A	06-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A	08-04-1983	Yoshihiro et al.		
		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32163	07-23-1998	Tai et al.		

Examiner Signature	<i>Brandi Thomas</i>	Date Considered	<i>9/2/05</i>
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	10/666.002
		Filing Date	9/17/03
		First Named Inventor	Shi
		Art Unit	Not Yet Assigned 2873
		Examiner Name	Not Yet Assigned Thomas
Sheet	2	of	6
		Attorney Docket Number	P120-US

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
BNT		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leung, et al.	
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		US- 4,551,197	11/05/85	Guilmette, et al.	
BNT		US- 6,299,864	9/18/01	Patel, et al.	
		US- 2004/0069747	4/15/04	Patel, et al.	
		US- 2002/0195423	12/26/02	Patel, et al.	
		US- 2004/0035821	2/26/04	Doan, et al.	
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Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)			
BNT		JP-1997/09251981-A	09-22-1997	Kazuaki et al.	
		JP-1998/10313128-A	11-24-1998	Hanmin et al.	
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.	
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		JP-1987/62071217-A	04-01-1987	Toru, et al.	
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		JP-1986/61053732-A	03-17-1986	Arata et al.	
		JP-1986/61134019-A	06-21-1986	Shinji et al.	
		JP-1986/61181131-A	08-13-1986	Shinji et al.	

Examiner Signature	Brand Thomas	Date Considered	9/2/05
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Substitute for form 1449A/PTO

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Sheet 3 of 6

**Complete if Known**

Application Number	10/666.002
Filing Date	9/17/03
First Named Inventor	Shi
Art Unit	Not Yet Assigned <b>2873</b>
Examiner Name	Not Yet Assigned <b>Thomas</b>
Attorney Docket Number	P120-US

**U.S. PATENT DOCUMENTS**

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			Application Number	10/666,002	
			Filing Date	9/17/03	
			First Named Inventor	Shi	
			Group Art Unit	Not Yet Assigned 2873	
			Examiner Name	Not Yet Assigned Thomas	
Sheet	4	of	6	Attorney Docket Number	P120-US

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Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
BNT		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
		GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
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		IBBOTSON et al., "Comparison of XeF2 and F-atom Reactions with Si and SiO2", Applied Physics Letter, Vol. 44, 1129 (1984).	
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		VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
BNT		WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	

Examiner Signature	Brandi Thomas	Date Considered	9/12/05
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Substitute for form 1449B/PTO			<b>Complete if Known</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			Application Number	10/666.002	
			Filing Date	9/17/03	
			First Named Inventor	Shi	
			Group Art Unit	Not Yet Assigned <i>2873</i>	
			Examiner Name	Not Yet Assigned <i>Thomas</i>	
			Attorney Docket Number	P120-US	
Sheet	5	of	6		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
<i>BNT</i>		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
<i>BNT</i>		WINTERS et al., "The Etching of Silicon with XeF <sub>2</sub> Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
<i>BNT</i>		XACTIX, Inc., Marketing Brochure (June 27, 1999).	
<i>BNT</i>		"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
<i>BNT</i>		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
<i>BNT</i>		BASSOM et al., "Modeling and Optimizing XeF <sub>2</sub> -enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
<i>BNT</i>		KOHLER et al., "Fabrication of Microlenses by Plasmaless Isotropic Etching Combined with Plastic Moulding", Sens. Actuators A, Phys. (Switzerland), Vol. A53, No. 1-3 (May 1996), pp. 361-363 (abstract only).	
<i>BNT</i>		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millenium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
<i>BNT</i>		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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		Filing Date	9/17/03
		First Named Inventor	Shi
		Group Art Unit	Not Yet Assigned 2873
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		SUGANO et al., "Study on XeF <sub>2</sub> Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Milet 1.5- $\mu$ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
BNT		SEBEL et al., "Etching of Si Through a Thick Condensed XeF <sub>2</sub> Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

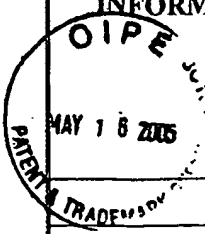
Examiner Signature	Brand Thomas	Date Considered	9/12/05
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<b>INFORMATION DISCLOSURE CITATION</b>  <b>PTO-1449</b>  SHEET 1 OF 1	ATTY. DOCKET NO. P120-US	SERIAL NO. 10/666,002
	APPLICANT Hongqin Shi, et al.	
	FILING DATE 9/17/03	GROUP <del>Not Yet Assigned</del> 2873



**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
BNT	5,604,367	02-1997	Yang			
BNT	6,153,115	11-2000	Le, et al.			
BNT	6,162,367	12-2000	Tai, et al.			

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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						<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

EXAMINER <i>Brand Shoma</i>	DATE CONSIDERED <i>9/2/05</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.